

What Is Claimed Is:

1. A semiconductor component, comprising:
 - a semiconductor substrate;
 - a covering layer, above a hollow space, made from porous silicon material, wherein the covering layer includes a first section and a second section, a first earlier pore structure of the first section differing from a second earlier pore structure of the second section.
2. The semiconductor component of claim 1, wherein the semiconductor component includes a pressure sensor.
3. The semiconductor component of claim 1, wherein the first earlier pore structure in the first section is oriented substantially perpendicularly to a main substrate plane, and the second earlier pore structure in the second section is oriented substantially in parallel to the main substrate plane.
4. The semiconductor component of claim 1, wherein one of the second earlier pore structure in the second section is provided as a mesoporous structure, the second earlier pore structure in the second section is provided as a nanoporous structure, and the pore structure in the second section has a higher porosity than in the first section.
5. The semiconductor component of claim 1, wherein the semiconductor substrate includes silicon.
6. The semiconductor component of claim 1, further comprising:
 - a diaphragm layer above the covering layer.
7. A method for fabricating a semiconductor component, the method comprising:
 - providing a covering layer having a first section and a second section so that the second section is covered by a

cover when pores are provided, so that the pores form underneath the cover;

wherein the semiconductor component includes a semiconductor substrate, and the covering layer, above a hollow space, made from porous silicon material, and a first earlier pore structure of the first section differs from a second earlier pore structure of the second section.

8. The method of claim 7, wherein the second section is less heavily doped than the first section, so that the pores in the second section are smaller than in the first section.

9. The method of claim 8, wherein the covering layer is provided in one of lines, points, and small squares.

10. The method of claim 7, wherein the covering layer is provided in one of lines, points, and small squares.